

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	232	438/517.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:36
L2	10	(SOI same epitaxial and CMOS).clm.	US-PGPUB	OR	ON	2005/10/14 14:44
S1	70	super adj steep adj retrograde	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/13 18:32
S2	25	((super adj steep adj retrograde) ssrw) and soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:20
S3	7477	soi and trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:21
S4	3328	soi and trench\$2 and (fet mosfet nmos pmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:21
S5	495	soi and (isolation adj trench\$2) and (fet mosfet nmos pmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:21
S6	36	soi and (isolation adj trench\$2) and (fet mosfet nmos pmos) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:22
S7	36	soi and (isolation adj trench\$2) and (fet mosfet nmos pmos) and (ground adj plane) and thin\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:23
S8	992	soi and (isolation adj trench\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:45

S9	1563	soi and isolation and (island islands)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:45
S10	548	(soi with thin\$3) and isolation and (island islands)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:45
S11	392	retrograde adj well	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:57
S12	66	retrograde adj well and soi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 17:57
S13	2735	"438"/\$.ccls. and (SOI same (thin thinner thinning))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 20:59
S14	46	"438"/\$.ccls. and (SOI same (thin thinner thinning)) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:03
S15	9	"438"/\$.ccls. and (SOI same (thinner thinning thinning)) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:11
S16	4	"438"/\$.ccls. and (SOI same (thinned)) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:19
S17	15	"257"/\$.ccls. and (SOI same (thinning thinner thinned)) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:20
S18	36	SOI and (isolation adj trench) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:34

S19	36	SOI and (isolation adj trenches) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:34
S20	44	"438"/\$.ccls. and SOI and (trenches) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:38
S21	70	"257"/\$.ccls. and SOI and (trenches) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/01 21:41
S22	119	"257"/\$.ccls. and SOI and (isolation) and (ground adj plane)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:26
S23	3	"257"/\$.ccls. and SOI and (isolation) and (ground adj regions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:28
S24	2	"438"/\$.ccls. and SOI and (isolation) and (ground adj regions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:28
S25	4	SOI and (isolation) and (ground adj regions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:29
S26	6	SOI and (trench trenches) and (ground adj regions)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:29
S27	902	SOI and (pad with (oxide and nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:53
S28	700	SOI and (pad near4 (oxide and nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:54

S29	188	SOI and (pad adj nitride) and (pad adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/02 09:54
S30	7877	SOI and epitaxial	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 18:33
S31	3267	SOI and epitaxial and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/13 18:33
S32	1650	SOI same epitaxial and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:44
S33	1650	(SOI same epitaxial) and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:16
S34	685	257/351.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:25
S35	2760	257/347.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:53
S36	249	438/153.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:54
S37	984	438/153,154.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:54
S38	2395	438/153,154,149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 09:54

S39	984	438/153,154.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:20
S40	1499	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 13:49
S41	1053	438/479.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 14:27